

## LISTING OF THE CLAIMS

1 (amended): A method of partially plating a substrate for electronic devices, comprising arranging metal balls having a diameter of 60 to 150  $\mu\text{m}$  at selected portions of a substrate for mounting ~~semiconductor~~ electronic devices thereon, and adhering or bonding the metal balls thereto, and melting the metal balls to form a plated layer thermally diffused with the substrate, thereby selectively plating the selected portions of the substrate for electronic devices with a different metal with no plating solutions used.

2 (amended): The method of partially plating a substrate for electronic devices as claimed in claim 1, wherein the method comprises provisionally arranging and holding the metal balls on a surface of an arrangement base plate having through holes provided at positions corresponding to the portions to be plated of the substrate for electronic devices, with said surface of said arrangement base plate facing downward during said provisionally arranging and holding procedure, transferring the arrangement base plate above the substrate for mounting electronic devices, and adhering or bonding the metal balls provisionally arranged at and held by the through holes to the portions to be plated, respectively.

3 (amended): The method of partially plating a substrate for electronic devices as claimed in claim 2, wherein, in the provisionally arranging and holding procedure, excess metal balls adhering to the arrangement base plate or the metal balls which are provisionally held by the ~~substrate~~ arrangement base plate are removed by applying

vibrations to the arrangement base plate, thereby provisionally arranging and holding the metal balls.

4 (previously presented): The method of partially plating a substrate for electronic devices as claimed in claim 3, wherein the vibrations are ultrasonic vibrations.

Claim 5: (canceled).

6 (previously presented): The method of partially plating a substrate for electronic devices as claimed in claim 1, wherein the metal balls are selected from Au, Ag, Pd, Pt, Ni or Cr, and balls are melted by partial heating.

7 (previously presented): The method of partially plating a substrate for electronic devices as claimed in claim 1, wherein the substrate for electronic devices is an insulating resin substrate or a polyimide tape, and the selected portions are wiring composed of copper.

8 (previously presented): The method of partially plating a substrate for electronic devices as claimed in claim 1, wherein the substrate for electronic devices is made of a ceramic material, and the selected portions are wiring composed of copper.

9 (previously presented): The method of partially plating a substrate for electronic devices as claimed in claim 1, wherein the substrate for electronic devices is a lead frame composed of copper or iron alloy, and the leads of the lead frame are partially plated.

10 (previously presented): The method of partially plating a substrate for electronic devices as claimed in claim 1, wherein the metal balls are solder, and the metal balls are melted by reflowing to selectively plate the

selected portions of the substrate for electronic devices and with a metal layer different from a substrate metal and the ball metal intervening between the substrate metal and the ball metal.

11 (previously presented): The method of partially plating a substrate for electronic devices as claimed in claim 1, wherein the metal balls are selected from Sn alloy or In alloy and the selected metal balls are melted by reflowing to selectively plate the selected portions of the substrate for electronic devices with a different metal.